

Rewrite claims 8, 14, 32 and 45 as follows:

A1
8. (Amended) The RF amplifier of claim 7 wherein said bipolar transistor is an insulated gate bipolar transistor.

A2
Sub B2
14. (Amended) The RF power amplifier of claim 1 wherein the filter is a first filter and further comprising:
a second filter coupled to said second conducting terminal via said resonant inductor circuit wherein the level of said output of said amplifier is approximately at RF ground potential and wherein the level of said output of said amplifier is not affected by said second filter.

A3
Sub B3
32. (Amended) The RF power amplifier of claim 21 wherein the filter is a first filter and further comprising:
a second filter coupled to said source terminal via said resonant inductor circuit wherein the level of said output of said amplifier is approximately at RF ground potential and wherein the level of said output of said amplifier is not affected by said second filter.

A4
Sub B5
45. (Amended) The RF power amplifier of claim 34 wherein the filter is a first filter and further comprising: